Switching Regulator - Automotive Buck

1.2 A, 2 MHz

The NCV890100 is a fixed-frequency, monolithic, Buck switching regulator intended for Automotive, battery-connected applications that must operate with up to a 36 V input supply. The regulator is suitable for systems with low noise and small form factor requirements often encountered in automotive driver information systems. The NCV890100 is capable of converting the typical 4.5 V to 18 V automotive input voltage range to outputs as low as 3.3 V at a constant switching frequency above the sensitive AM band, eliminating the need for costly filters and EMI countermeasures. The NCV890100 also provides several protection features expected in Automotive power supply systems such as current limit, short circuit protection, and thermal shutdown. In addition, the high switching frequency produces low output voltage ripple even when using small inductor values and an all-ceramic output filter capacitor – forming a space–efficient switching regulator solution.

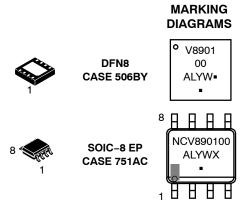
Features

- Internal N-Channel Power Switch
- Low V_{IN} Operation Down to 4.5 V
- High V_{IN} Operation to 36 V
- Withstands Load Dump to 40 V
- 2 MHz Free-running Switching Frequency
- Logic Level Enable Input Can be Directly Tied to Battery
- 1.4 A (min) Cycle-by-Cycle Peak Current Limit
- Short Circuit Protection Enhanced by Frequency Foldback
- ±1.75% Output Voltage Tolerance
- Output Voltage Adjustable Down to 0.8 V
- 1.4 Millisecond Internal Soft-Start
- Thermal Shutdown (TSD)
- Low Shutdown Current
- Wettable Flanks DFN
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable



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A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week
■ Pb-Free Device

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 17 of this data sheet.

• These Devices are Pb-Free and are RoHS Compliant

Applications

- Audio
- Infotainment
- Safety Vision Systems
- Instrumentation

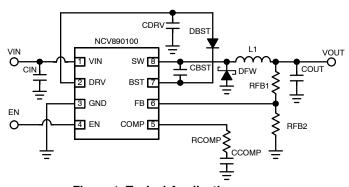


Figure 1. Typical Application

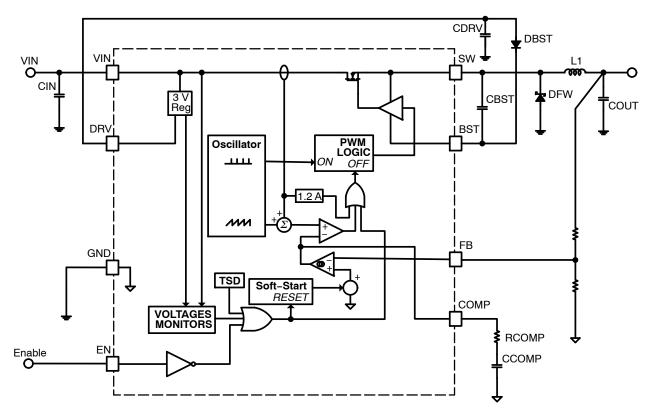


Figure 2. NCV890100 Block Diagram

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Min/Max Voltage VIN		-0.3 to 40	V
Max Voltage VIN to SW		40	V
Min/Max Voltage SW		-0.7 to 40	V
Min Voltage SW – 20ns		-3.0	V
Min/Max Voltage BST		-0.3 to 40	
Min/Max Voltage BST to SW		-0.3 to 3.6	V
Min/Max Voltage on EN		-0.3 to 40	V
Min/Max Voltage COMP		-0.3 to 2	V
Min/Max Voltage FB		-0.3 to 18	V
Min/Max Voltage DRV		-0.3 to 3.6	V
Thermal Resistance, 3x3 DFN Junction-to-Ambient*	$R_{ hetaJA}$	50	°C/W
Thermal Resistance, SOIC-8 EP Junction-to-Ambient*	$R_{ hetaJA}$	40	°C/W
Storage Temperature range		-55 to +150	°C
Operating Junction Temperature Range	TJ	-40 to +150	°C
ESD withstand Voltage Human Body Model Machine Model Charge Device Model	V _{ESD}	2.0 200 >1.0	kV V kV
Moisture Sensitivity, DFN8	MSL	Level 1	
Moisture Sensitivity, SOIC-8 EP	MSL	Level 2	
Peak Reflow Soldering Temperature		260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Mounted on 1 sq. in. of a 4-layer PCB with 1 oz. copper thickness.

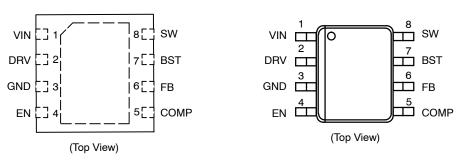


Figure 3. Pin Connections

PIN FUNCTION DESCRIPTIONS

Pin No.	Symbol	Description
1	VIN	Input voltage from battery. Place an input filter capacitor in close proximity to this pin.
2	DRV	Output voltage to provide a regulated voltage to the Power Switch gate driver.
3	GND	Battery return, and output voltage ground reference.
4	EN	This TTL compatible Enable input allows the direct connection of Battery as the enable signal. Grounding this input stops switching and reduces quiescent current draw to a minimum.
5	COMP	Error Amplifier output, for tailoring transient response with external compensation components.
6	FB	Feedback input pin to program output voltage, and detect pre-charged or shorted output conditions.
7	BST	Bootstrap input provides drive voltage higher than VIN to the N-channel Power Switch for optimum switch R _{DS(on)} and highest efficiency.
8	SW	Switching node of the Regulator. Connect the output inductor and cathode of the freewheeling diode to this pin.
Exposed Pad		Connect to Pin 3 (electrical ground) and to a low thermal resistance path to the ambient temperature environment.

ELECTRICAL CHARACTERISTICS (V_{IN} = 4.5 V to 28 V, V_{EN} = 5 V, V_{BST} = V_{SW} + 3.0 V, C_{DRV} = 0.1 μ F, Min/Max values are valid for the temperature range $-40^{\circ}\text{C} \leq T_J \leq 150^{\circ}\text{C}$ unless noted otherwise, and are guaranteed by test, design or statistical correlation.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
QUIESCENT CURRENT				-	-	
Quiescent Current, shutdown	I_{qSD}	V_{IN} = 13.2 V, V_{EN} = 0 V, T_{J} = 25°C			5	μА
Quiescent Current, enabled	I _{qEN}	V _{IN} = 13.2 V			3	mA
UNDERVOLTAGE LOCKOUT - VIN (UVL	_O)					•
UVLO Start Threshold	V _{UVLSTT}	V _{IN} rising	4.1		4.5	V
UVLO Stop Threshold	V _{UVLSTP}	V _{IN} falling	3.9		4.4	V
UVLO Hysteresis	V _{UVLOHY}		0.1		0.2	V
ENABLE (EN)	•					•
Logic Low	V _{ENLO}		0.8			V
Logic High	V _{ENHI}				2	V
Input Current	I _{EN}		8		30	μА
SOFT-START (SS)	•					•
Soft-Start Completion Time	t _{SS}		0.8	1.4	2.0	ms
VOLTAGE REFERENCE						
FB Pin Voltage during regulation	V_{FBR}	COMP shorted to FB	0.786	0.8	0.814	V
ERROR AMPLIFIER	•					
FB Bias Current	I _{FBBIAS}	V _{FB} = 0.8 V	0.25		1	μΑ
Transconductance	gm gm(HV)	V _{COMP} = 1.3 V 4.5 V < V _{IN} < 18 V 20 V < V _{IN} < 28 V	0.6 0.3	1 0.5	1.5 0.75	mmho
Output Resistance	R _{OUT}			1.4		ΜΩ
COMP Source Current Limit	Isource	V _{FB} = 0.63 V, V _{COMP} = 1.3 V 4.5 V < V _{IN} < 18 V 20 V < V _{IN} < 28 V		75 40		μΑ
COMP Sink Current Limit	I _{SINK}	V _{FB} = 0.97 V, V _{COMP} = 1.3 V 4.5 V < V _{IN} < 18 V 20 V < V _{IN} < 28 V		75 40		μΑ
Minimum COMP voltage	V _{CMPMIN}	V _{FB} = 0.97 V	0.2		0.7	V
OSCILLATOR	•					
Frequency	F _{SW} F _{SW(HV)}	4.5 < V _{IN} < 18 V 20 V < V _{IN} < 28 V	1.8 0.9	2.0 1.0	2.2 1.1	MHz
VIN FREQUENCY FOLDBACK MONITO	R					
Frequency Foldback Threshold V _{IN} rising V _{IN} falling	V _{FLDUP} V _{FLDDN}	V _{FB} = 0.63 V	18.4 18		20 19.8	V
Frequency Foldback Hysteresis	V_{FLDHY}		0.2	0.3	0.4	V
SLOPE COMPENSATION						
Ramp Slope (Note 1) (With respect to switch current)	S _{ramp} S _{ramp(HV)}	4.5 < V _{IN} < 18 V 20 V < V _{IN} < 28 V	0.7 0.25		1.3 0.6	A/μs

^{1.} Not tested in production. Limits are guaranteed by design.

ELECTRICAL CHARACTERISTICS (V_{IN} = 4.5 V to 28 V, V_{EN} = 5 V, V_{BST} = V_{SW} + 3.0 V, C_{DRV} = 0.1 μ F, Min/Max values are valid for the temperature range $-40^{\circ}\text{C} \leq T_J \leq 150^{\circ}\text{C}$ unless noted otherwise, and are guaranteed by test, design or statistical correlation.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
POWER SWITCH							
ON Resistance	R _{DSON}	V _{BST} = V _{SW} + 3.0 V			650	mΩ	
Leakage current VIN to SW	I _{LKSW}	V _{EN} = 0 V, V _{SW} = 0, V _{IN} = 18 V			10	μΑ	
Minimum ON Time	t _{ONMIN}	Measured at SW pin	45		70	ns	
Minimum OFF Time	t _{OFFMIN}	Measured at SW pin At F _{SW} = 2 MHz (normal) At F _{SW} = 500 kHz (max duty cycle)	30	30 50	70	ns	
PEAK CURRENT LIMIT	PEAK CURRENT LIMIT						
Current Limit Threshold	I _{LIM}		1.4	1.55	1.7	Α	
SHORT CIRCUIT FREQUENCY FOLDBACK							
Lowest Foldback Frequency Lowest Foldback Frequency – High V _{in} Hiccup Mode	F _{SWAF} F _{SWAFHV} F _{SWHIC}	$V_{FB} = 0 \text{ V}, 4.5 \text{ V} < V_{IN} < 18 \text{ V} \\ V_{FB} = 0 \text{ V}, 20 \text{ V} < V_{IN} < 28 \text{ V} \\ V_{FB} = 0 \text{ V}$	400 200 24	500 250 32	600 300 40	kHz	
GATE VOLTAGE SUPPLY (DRV pin)	GATE VOLTAGE SUPPLY (DRV pin)						
Output Voltage	V_{DRV}		3.1	3.3	3.5	V	
DRV POR Start Threshold	V _{DRVSTT}		2.7	2.9	3.05	V	
DRV POR Stop Threshold	V _{DRVSTP}		2.5	2.8	3.0	V	
DRV Current Limit	I _{DRVLIM}	V _{DRV} = 0 V	16		45	mA	
OUTPUT PRECHARGE DETECTOR							
Threshold Voltage	V _{SSEN}		20	35	50	mV	
THERMAL SHUTDOWN							
Activation Temperature (Note 1)	T _{SD}		150		190	°C	
Hysteresis (Note 1)	T _{HYS}		5		20	°C	

^{1.} Not tested in production. Limits are guaranteed by design.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS CURVES

V_{UVLSTP}. UVLO STOP THRESHOLD (V)

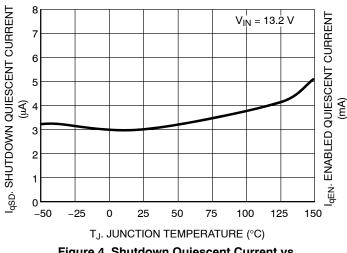


Figure 4. Shutdown Quiescent Current vs.
Junction Temperature

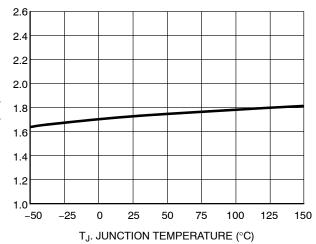


Figure 5. Enabled Quiescent Current vs.
Junction Temperature

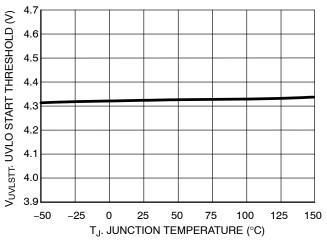


Figure 6. UVLO Start Threshold vs. Junction Temperature

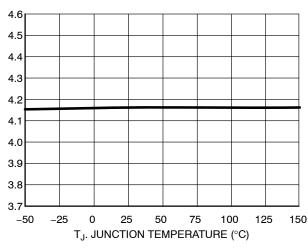


Figure 7. UVLO Stop Threshold vs. Junction Temperature

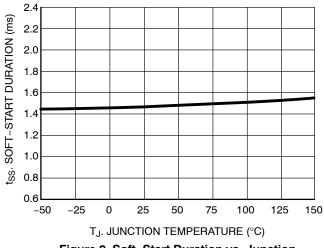


Figure 8. Soft-Start Duration vs. Junction Temperature

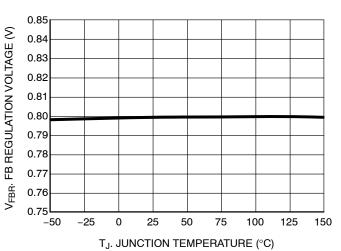
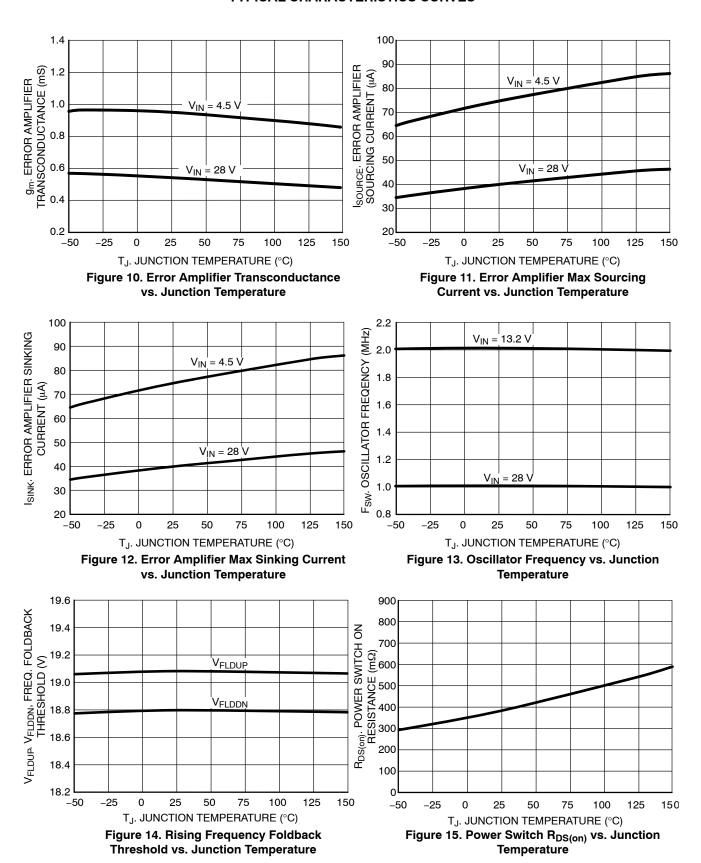
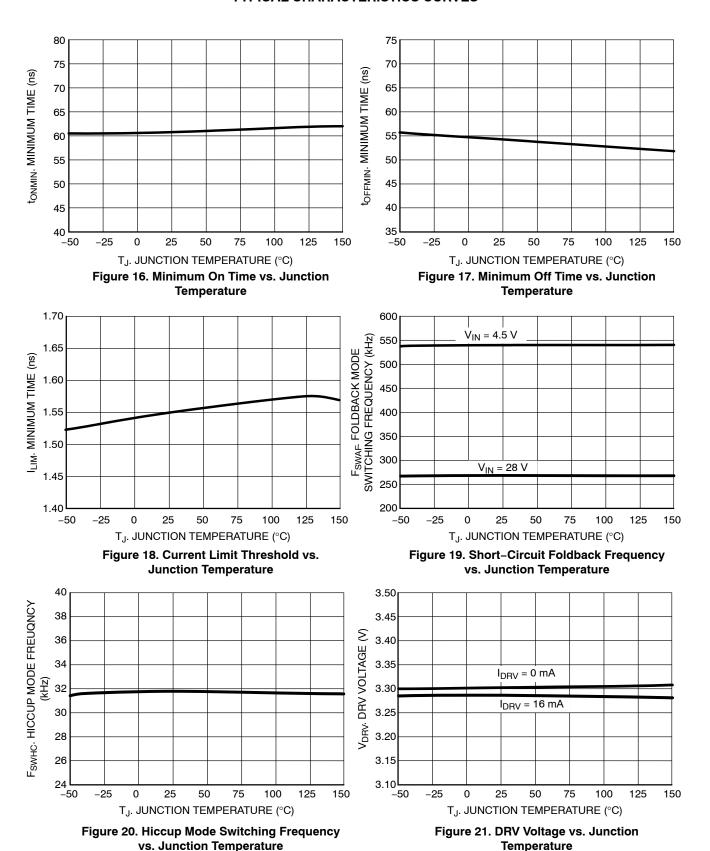


Figure 9. FB Regulation Voltage vs. Junction Temperature

TYPICAL CHARACTERISTICS CURVES



TYPICAL CHARACTERISTICS CURVES



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TYPICAL CHARACTERISTICS CURVES

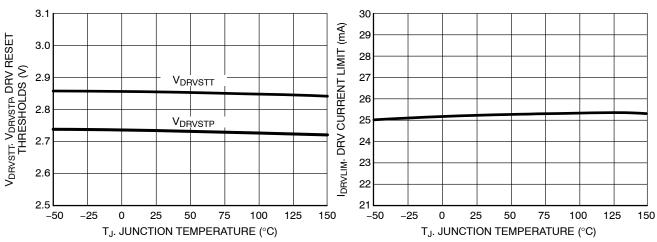


Figure 22. DRV Reset Threshold vs. Junction Temperature

Figure 23. DRV Current Limit vs. Junction Temperature

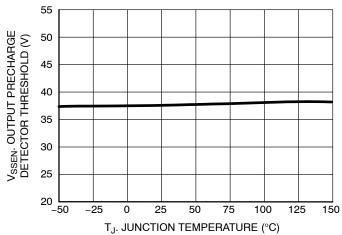


Figure 24. Output Precharge Detector Threshold vs. Junction Temperature

GENERAL INFORMATION

INPUT VOLTAGE

An Undervoltage Lockout (UVLO) circuit monitors the input, and inhibits switching and resets the Soft–start circuit if there is insufficient voltage for proper regulation. The NCV890100 can regulate a 3.3 V output with input voltages above 4.5 V and a 5.0 V output with an input above 6.5 V.

The NCV890100 withstands input voltages up to 40 V.

To limit the power lost in generating the drive voltage for the Power Switch, the switching frequency is reduced by a factor of 2 when the input voltage exceeds the V_{IN} Frequency Foldback threshold V_{FLDUP} (see Figure 25). Frequency reduction is automatically terminated when the input voltage drops back below the V_{IN} Frequency Foldback threshold V_{FLDDN} .

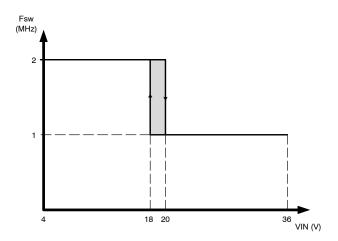


Figure 25. NCV890100 Switching Frequency Reduction at High Input Voltage

ENABLE

The NCV890100 is designed to accept either a logic level signal or battery voltage as an Enable signal. EN low induces a 'sleep mode' which shuts off the regulator and minimizes its supply current to a couple of μA typically (I_{qSD}) by disabling all functions. Upon enabling, voltage is established at the DRV pin, followed by a soft–start of the switching regulator output.

SOFT-START

Upon being enabled or released from a fault condition, and after the DRV voltage is established, a soft–start circuit ramps the switching regulator error amplifier reference voltage to the final value. During soft–start, the average switching frequency is lower than its normal mode value (typically 2 MHz) until the output voltage approaches regulation.

SLOPE COMPENSATION

A fixed slope compensation signal is generated internally and added to the sensed current to avoid increased output voltage ripple due to bifurcation of inductor ripple current at duty cycles above 50%. The fixed amplitude of the slope compensation signal requires the inductor to be greater than a minimum value, depending on output voltage, in order to avoid sub–harmonic oscillations. For 3.3 V and 5 V output voltages, the recommended inductor value is 4.7 µH.

SHORT CIRCUIT FREQUENCY FOLDBACK

During severe output overloads or short circuits, the NCV890100 automatically reduces its switching frequency. This creates duty cycles small enough to limit the peak current in the power components, while maintaining the ability to automatically reestablish the output voltage if the overload is removed. If the current is still too high after the switching frequency folds back to 500 kHz, the regulator enters an auto-recovery burst mode that further reduces the dissipated power.

CURRENT LIMITING

Due to the ripple on the inductor current, the average output current of a buck converter is lower than the peak current setpoint of the regulator. Figure 26 shows – for a $4.7~\mu H$ inductor – how the variation of inductor peak current with input voltage affects the maximum DC current the NCV890100 can deliver to a load.

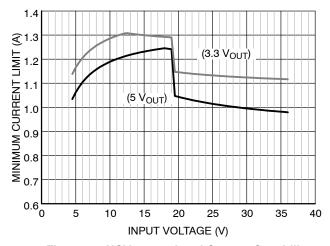


Figure 26. NCV890100 Load Current Capability with 4.7 µH Inductor

BOOTSTRAP

At the DRV pin an internal regulator provides a ground–referenced voltage to an external capacitor (C_{DRV}), to allow fast recharge of the external bootstrap capacitor (C_{BST}) used to supply power to the power switch gate driver. If the voltage at the DRV pin goes below the DRV UVLO Threshold V_{DRVSTP} , switching is inhibited and the Soft–start circuit is reset, until the DRV pin voltage goes back up above V_{DRVSTT} .

In order for the bootstrap capacitor to stay charged, the Switch node needs to be pulled down to ground regularly. In very light load condition, the NCV890100 skips switching cycles to ensure the output voltage stays regulated. When the skip cycle repetition frequency gets too low, the bootstrap voltage collapses and the regulator stops switching. Practically, this means that the NCV890100 needs a minimum load to operate correctly. Figure 27 shows the minimum current requirements for different input and output voltages.

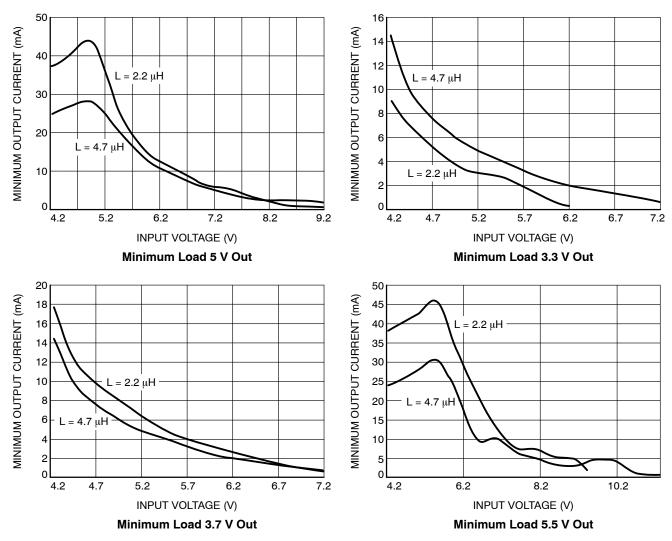
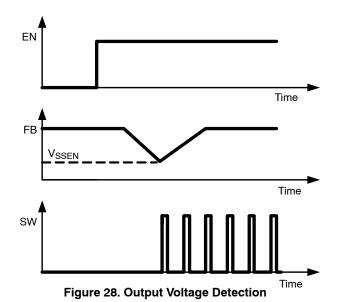


Figure 27. Minimum Load Current with Different Input and Output Voltages

OUTPUT PRECHARGE DETECTION

Prior to Soft-start, the FB pin is monitored to ensure the SW voltage is low enough to have charged the external bootstrap capacitor (C_{BST}). If the FB pin is higher than V_{SSEN}, restart is delayed until the output has discharged. Figure 28 shows the IC starts to switch after the voltage on FB pin reaches VSSEN, even the EN pin is high. After the IC is switching, the FB pin follows the soft starts reference to reach the final set point.



THERMAL SHUTDOWN

A thermal shutdown circuit inhibits switching, resets the Soft-start circuit, and removes DRV voltage if internal temperature exceeds a safe level. Switching is automatically restored when temperature returns to a safe level.

MINIMUM DROPOUT VOLTAGE

When operating at low input voltages, two parameters play a major role in imposing a minimum voltage drop across the regulator: the minimum off time (that sets the maximum duty cycle), and the on state resistance.

When operating in continuous conduction mode (CCM), the output voltage is equal to the input voltage multiplied by the duty ratio. Because the NCV890100 needs a sufficient bootstrap voltage to operate, its duty cycle cannot be 100%: it needs a minimum off time (t_{OFFmin}) to periodically re–fuel the bootstrap capacitor C_{BST} . This imposes a maximum duty ratio $D_{MAX} = 1 - t_{OFFmin}.F_{SW(min)}$, with the switching frequency being folded back down to $F_{SW(min)} = 500$ kHz to keep regulating at the lowest input voltage possible.

The drop due to the on-state resistance is simply the voltage drop across the Switch resistance R_{DSON} at the given output current: $V_{SWdrop} = I_{OUT}.R_{DSon}$.

Which leads to the maximum output voltage in low Vin condition: $V_{OUT} = D_{MAX}.V_{IN(min)} - V_{SWdrop}$

EXPOSED PAD

The exposed pad (EPAD) on the back of the package must be electrically connected to the electrical ground (GND pin) for proper, noise–free operation.

DESIGN METHODOLOGY

The NCV890100 being a fixed-frequency regulator with the switching element integrated, is optimized for one value of inductor. This value is set to 4.7 μ H, and the slope compensation is adjusted for this inductor. The only components left to be designed are the input and output capacitor and the freewheeling diode. Please refer to the design spreadsheet www.onsemi.com NCV890100 page that helps with the calculation.

Output capacitor:

The minimum output capacitor value can be calculated based on the specification for output voltage ripple:

$$C_{OUTmin} = \frac{\Delta I_{L}}{8 \cdot \Delta V_{OUT} \cdot F_{SW}}$$
 (eq. 1)

With

– ΔI_L the inductor ripple current:

$$\Delta I_{L} = \frac{V_{OUT} \cdot \left(1 - \frac{V_{OUT}}{V_{IN}}\right)}{L \cdot F_{SW}}$$
 (eq. 2)

– ΔV_{OUT} the desired voltage ripple.

However, the ESR of the output capacitor also contributes to the output voltage ripple, so to comply with the requirement, the ESR cannot exceed R_{ESRmax}:

$$R_{ESR\,max} = \frac{\Delta V_{OUT} \cdot L \cdot F_{SW}}{V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}}\right)}$$
 (eq. 3)

Finally, the output capacitor must be able to sustain the ac current (or RMS ripple current):

$$I_{OUTac} = \frac{\Delta I_{L}}{2\sqrt{3}}$$
 (eq. 4)

Typically, with the recommended 4.7 μH inductor, two ceramic capacitors of 10 μF each in parallel give very good results.

Freewheeling diode:

The diode must be chosen according to its maximum current and voltage ratings, and to thermal considerations.

As far as max ratings are concerned, the maximum reverse voltage the diode sees is the maximum input voltage (with some margin in case of ringing on the Switch node), and the maximum forward current the peak current limit of the NCV890100, I_{LIM}.

The power dissipated in the diode is P_{Dloss}:

$$P_{Dloss} = I_{OUT} \cdot \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \cdot V_{F} + I_{DRMS} \cdot R_{D} \quad (eq. 5)$$

with:

- I_{OUT} the average (dc) output current
- V_F the forward voltage of the diode
- I_{DRMS} the RMS current in the diode:

$$I_{DRMS} = \sqrt{(1 - D) \left(I_{OUT}^{2} + \frac{\Delta I_{L}^{2}}{12}\right)}$$
 (eq. 6)

 R_D the dynamic resistance of the diode (extracted from the V/I curve of the diode in its datasheet).

Then, knowing the thermal resistance of the package and the amount of heatsinking on the PCB, the temperature rise corresponding to this power dissipation can be estimated.

Input capacitor:

The input capacitor must sustain the RMS input ripple current I_{INac} :

$$I_{\text{INac}} = \frac{\Delta I_{\text{L}}}{2} \sqrt{\frac{\overline{D}}{3}}$$
 (eq. 7)

It can be designed in combination with an inductor to build an input filter to filter out the ripple current in the source, in order to reduce EMI conducted emissions.

For example, using a $4.7 \mu H$ input capacitor, it is easy to calculate that an inductor of 200 nH will ensure that the input filter has a cut-off frequency below 200 kHz (low enough to attenuate the 2 MHz ripple).

Error Amplifier and Loop Transfer Function

The error amplifier is a transconductance type amplifier. The output voltage of the error amplifier controls the peak inductor current at which the power switch shuts off. The Current Mode control method employed allows the use of a simple, type II compensation to optimize the dynamic response according to system requirements.

Figure 29 shows the error amplifier with the compensation components and the voltage feedback divider.

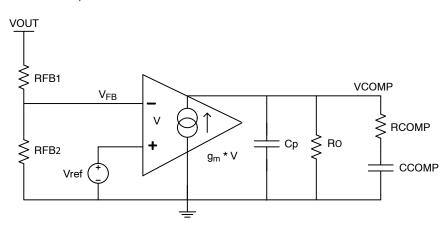


Figure 29. Feedback Compensator Network Model

The transfer function from VOUT to VCOMP is the product of the feedback voltage divider and the error amplifier.

$$Gdivider(s) = \frac{RFB2}{RFB1 + RFB2}$$
 (eq. 8)

$$Gerr_{amp(s)} = gm \cdot Ro \cdot \frac{1 + \frac{s}{\omega z}}{\left(1 + \frac{s}{\omega pl}\right)\left(1 + \frac{s}{\omega ph}\right)} \quad (eq. 9)$$

$$\omega z = \frac{1}{RCOMP \cdot CCOMP}$$
 (eq. 10)

$$\omega pI = \frac{1}{\text{Ro} \cdot \text{CCOMP}} \tag{eq. 11}$$

$$\omega ph = \frac{1}{RCOMP \cdot Cp}$$
 (eq. 12)

The output resistor Ro of the error amplifier is $1.4 \text{ M}\Omega$ and gm is 1 mA/V. The capacitor Cp is for rejecting noise at high frequency and is integrated inside the IC with a value of 18 pF.

The power stage transfer function (from Vcomp to output) is shown below:

$$Gps(s) = \frac{Rload}{Ri} \cdot \frac{1}{1 + \frac{Rload \cdot Tsw}{L} \cdot [Mc \cdot (1 - D) - 0.5]} \cdot \frac{1 + \frac{s}{\omega Z}}{1 + \frac{s}{\omega p}} \cdot Fh(s) \text{ (eq. 13)}$$

$$\omega p = \frac{1}{Resr \cdot Cout}$$
 (eq. 14)

$$\omega p = \frac{1}{\text{Rload} \cdot \text{Cout}} + \frac{\text{Mc} \cdot (1 - D) - 0.5}{\text{L} \cdot \text{Cout} \cdot \text{Fsw}} \quad (\text{eq. 15})$$

where

$$Mc = 1 + \frac{Se}{Sn}$$
 (eq. 16)

$$Sn = \frac{Vin - Vout}{L} \cdot Ri$$
 (eq. 17)

Ri represents the equivalent sensing resistor which has a value of 0.29 Ω , Se is the compensation slope which is 291.9 kV/S, Sn is the slope of the sensing resistor current during on time. Fh(s) represents the sampling effect from the current loop which has two poles at one half of the switching frequency:

Fh(s) =
$$\frac{1}{1 + \frac{s}{\omega n \cdot Qp} + \frac{s^2}{\omega n^2}}$$
 (eq. 18)

 $\omega n = \pi \cdot Fsw$

$$Qp = \frac{1}{\pi \cdot [Mc \cdot (1 - D) - 0.5]}$$
 (eq. 19)

The total loop transfer function is the product of power stage and feedback compensation network.

$$Gloop(s) = Gdivider(s) \cdot Gerr_{amp(s)} \cdot Gps(s)$$
 (eq. 20)

The bode plots of the open loop transfer function will show the gain and phase margin of the system. The compensation network is designed to make sure the system has enough phase margin and bandwidth.

Design of the Compensation Network

The function of the compensation network is to provide enough phase margin at crossover frequency to stabilize the system as well as to provide high gain at low frequency to eliminate the steady state error of the output voltage. Please refer to the design spreadsheet www.onsemi.com NCV890100 page that helps with the calculation.

The design steps will be introduced through an example. Example:

Vin = 15.5 V, Vout = 3.3 V, Rload = 2.75
$$\Omega$$
, Iout = 1.2 A,
L = 4.7 μ H, Cout = 20 μ F (Resr = 7 m Ω)

The reference voltage of the feedback signal is 0.8 V and to meet the minimum load requirements, select RFB1 = 100Ω , RFB2 = 31.6Ω .

From the specification, the power stage transfer function can be plotted as below:

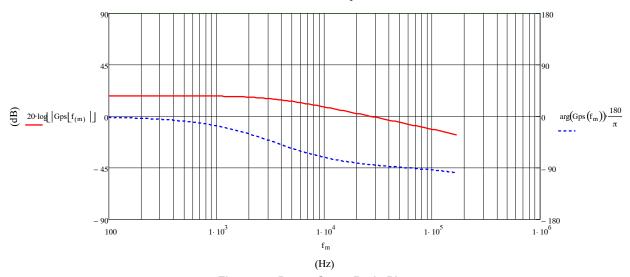


Figure 30. Power Stage Bode Plots

The crossover frequency is chosen to be Fc = 70 kHz, the power stage gain at this frequency is -8 dB (0.398) from calculation. Then the gain of the feedback compensation network must be 8 dB. Next is to decide the locations of one zero and one pole of the compensator. The zero is to provide phase boost at the crossover frequency and the pole is to reject the noise of high frequency. In this example, a zero is placed at 1/10 of the crossover frequency and a pole is placed at 1/5 of the switching frequency (Fsw = 2 MHz):

Fz = 7000 Hz, Fp = 400000 Hz,

RCOMP, CCOMP and Cp can be calculated from the following equations:

$$\label{eq:RCOMP} \text{RCOMP} = \frac{Fp \cdot gm}{(Fp - Fz) \cdot |Gps(Fc)|} \cdot \frac{Vout}{Vref} \cdot \frac{\sqrt{1 + \left(\frac{Fc}{Fp}\right)^2}}{\sqrt{1 + \left(\frac{Fz}{Fc}\right)^2}}$$

$$CCOMP = \frac{1}{2\pi \cdot Fz \cdot RCOMP}$$
 (eq. 22)

$$Cp = \frac{1}{2\pi \cdot Fp \cdot RCOMP}$$
 (eq. 23)

Note: there is an 18 pF capacitor at the output of the OTA integrated in the IC, and if a larger capacitor needs to be used, subtract this value from the calculated Cp. Figure 31 shows Cp is split into two capacitors. Cint is the 18 pF in the IC. Cext is the extra capacitor added outside the IC.

From the calculation:

So the feedback compensation network is as below:

RCOMP = $10.6 \text{ K}\Omega$, CCOMP = 2 nF, Cp = 37 pF

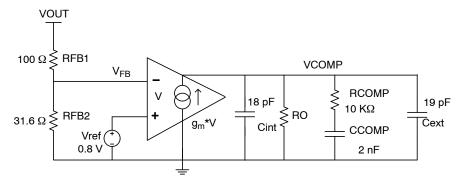


Figure 31. Example of the Feedback Compensation Network

Figure 32 shows the bode plot of the OTA compensator

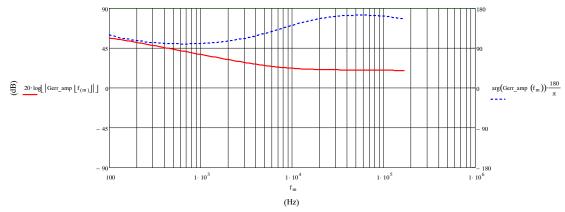


Figure 32. Bode Plot of the OTA Compensator

The total loop bode plot is as below:

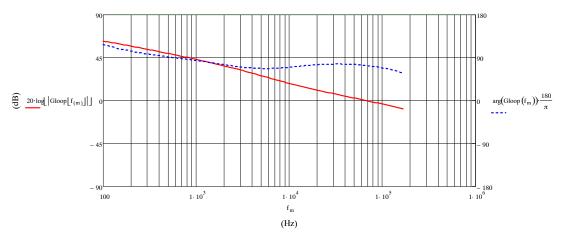


Figure 33. Bode Plot of the Total Loop

The crossover frequency is at 70 KHz and phase margin is 75 degrees.

PCB LAYOUT RECOMMENDATION

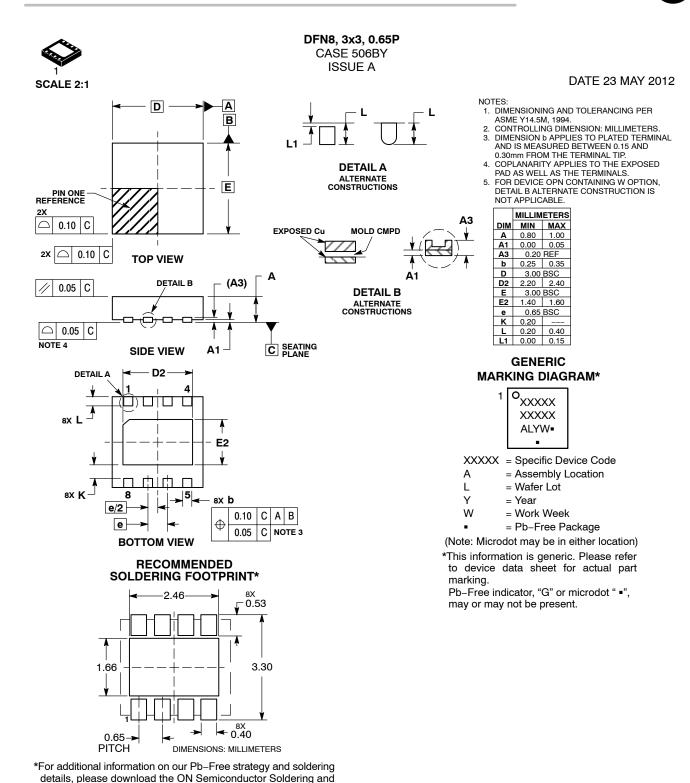
As with any switching power supplies, there are some guidelines to follow to optimize the layout of the printed circuit board for the NCV890100. However, because of the high switching frequency extra care has to be taken.

- Minimize the area of the power current loops:
 - Input capacitor → NCV890100 switch → Inductor
 → output capacitor → return through Ground
- Freewheeling diode → inductor → Output capacitor
 → return through ground
- Minimize the length of high impedance signals, and route them far away from the power loops:
 - Feedback trace
 - Comp trace

ORDERING INFORMATION

Device	Package	Shipping [†]
NCV890100MWTXG	DFN8 with wettable flanks (Pb-Free)	3000 / Tape & Reel
NCV890100PDR2G	SOIC-8 EP (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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DESCRIPTION:	DFN8, 3X3, 0.65P		PAGE 1 OF 1	

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Mounting Techniques Reference Manual, SOLDERRM/D.

MECHANICAL CASE OUTLINE

NOTES 4&5

HIH

TOP VIEW

SIDE VIEW

BOTTOM VIEW

NOTE 6

Е

NOTE 6 B

A1 NOTE 8

0.20 C D

△ 0.10 C D

NOTES 4&5

0.10 C D

8X b NOTES 3&7

♦ 0.25**№** C A-B D

0.10 C

С

SEATING PLANE





SOIC-8 EP CASE 751AC ISSUE D

DATE 02 APR 2019

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS

- 2. CONTROLLING DIMENSION: MILLING LERS
 3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 PROTRUSION SHALL BE 0.004 IN EXCESS OF MAXIMUM MATERIAL CONDITION.

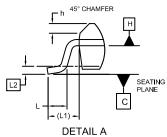
 4. DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE
 BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED
 0.006 PER SIDE. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR
 PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.010 mm PER SIDE.

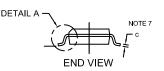
 5. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM.

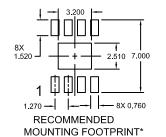
 DIMENSIONS D. AND E1 ADE DETERMINED AT THE OUTERPMOST EYTREMES.
- DIMENSIONS D AND E1 ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
- 6. DATUMS A AND B ARE TO BE DETERMINED AT DATUM H.
- 8. A1 IS DEFINED AND CAPPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 TO 0.25 FROM THE LEAD TIP.

 8. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.









	MILLIMETERS			
DIM	MIN.	NOM	MAX.	
Α	1.35	1.55	1.75	
A1	İ	0.05	0.10	
A2	1.35	1.50	1.65	
b	0.31	0.41	0.51	
С	0.17	0.21	0.23	
D	4.90 BSC			
E	6.00 BSC			
E1	3.90 BSC			
е	1.27 BSC			
F	2.24	2.72	3.20	
F1	0.15	0.20	0.25	
G	1.55	2.03	2.51	
G1	0.41	0.46	0.51	
h	0.25	0.38	0.50	
L	0.40	0.84	1.27	
L1	1.04 REF			
L2	0.25 REF			
Ø	0°	4°	8°	

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D."

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code = Assembly Location Υ = Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present and may be in either location. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOIC-8 EP		PAGE 1 OF 1	

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